



PBSS5330PA

30 V, 3 A PNP low V_{CEsat} (BISS) transistor

7 April 2015

Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

NPN complement: PBSS4330PA.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

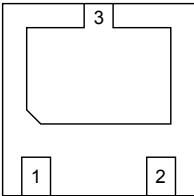
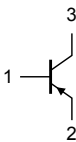
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-30	V
I _C	collector current		-	-	-3	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-5	A
R _{CEsat}	collector-emitter saturation resistance	I _C = -3 A; I _B = -300 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	75	107	mΩ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	 <p>Transparent top view</p> <p>DFN2020-3 (SOT1061)</p>	 <p>sym013</p>
2	E	emitter		
3	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5330PA	DFN2020-3	DFN2020-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061

7. Marking

Table 4. Marking codes

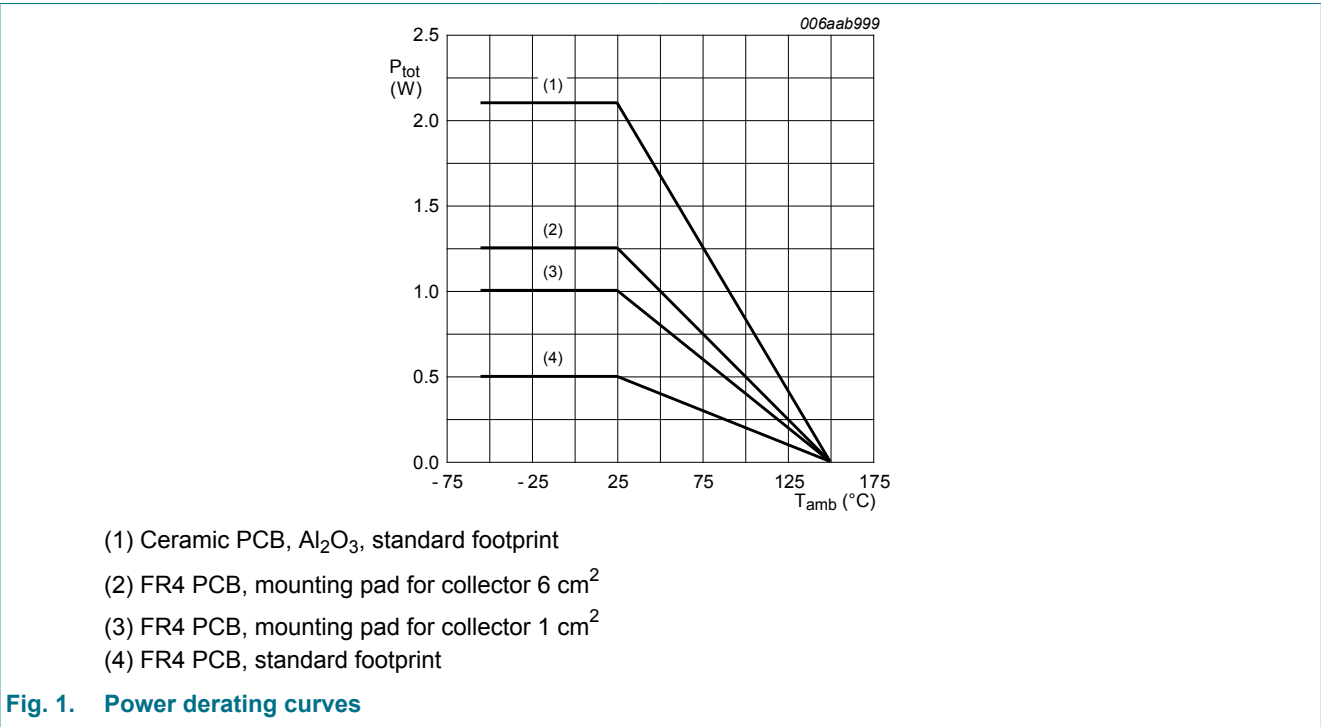
Type number	Marking code
PBSS5330PA	AJ

8. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-30	V
V _{CEO}	collector-emitter voltage	open base		-	-30	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-3	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-5	A
I _B	base current			-	-500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	500	mW
			[2]	-	1	W
			[3]	-	1.25	W
			[4]	-	2.1	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W
			[2]	-	-	125	K/W
			[3]	-	-	100	K/W
			[4]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

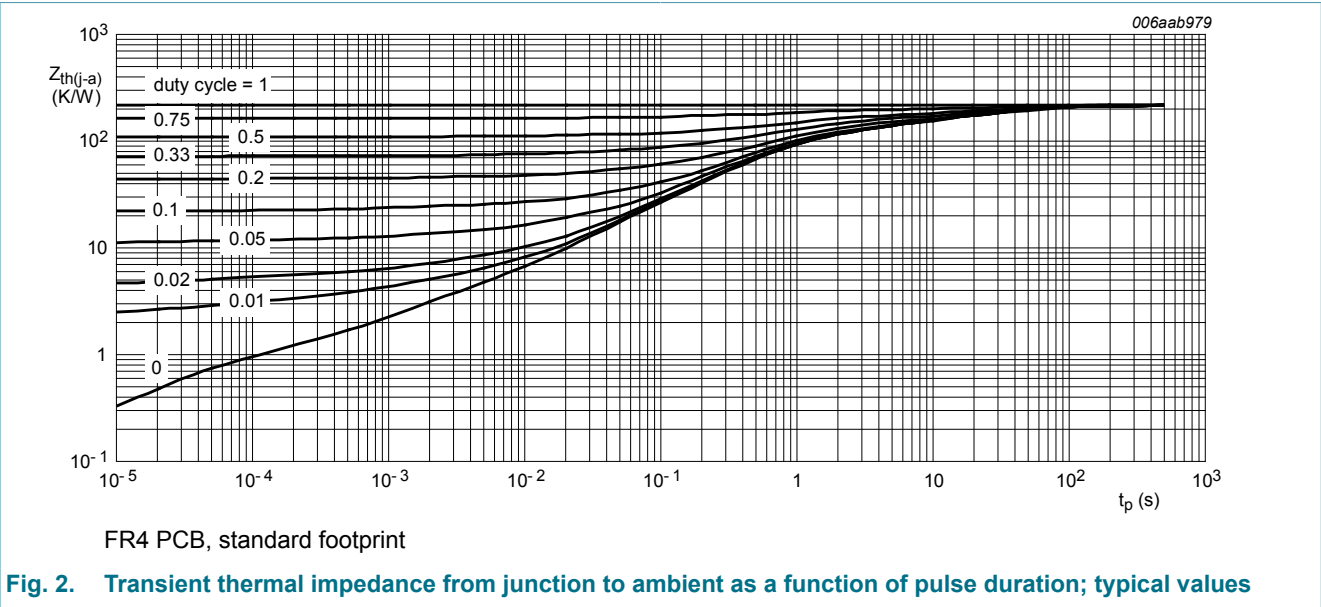
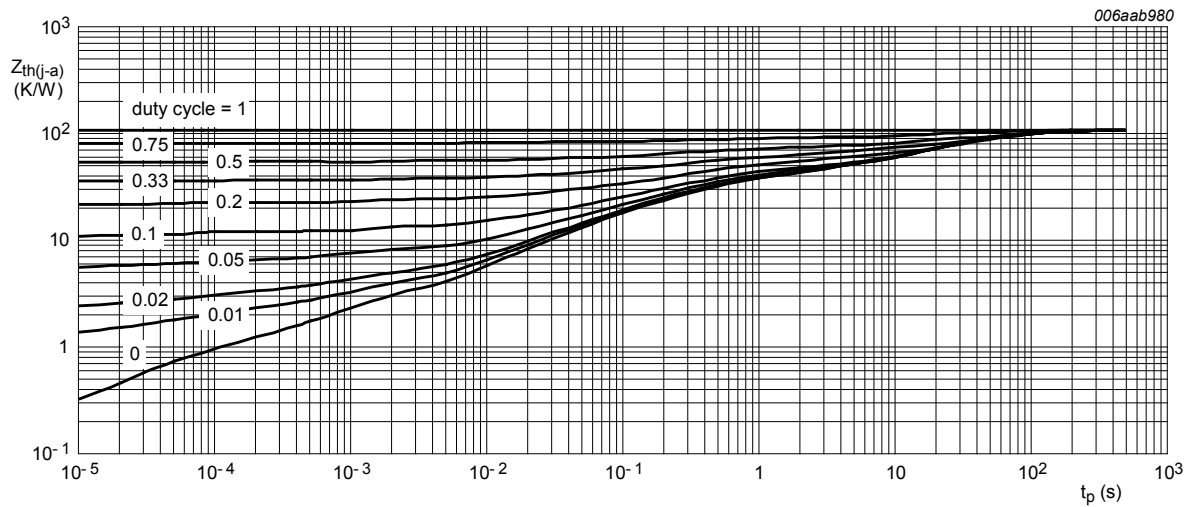
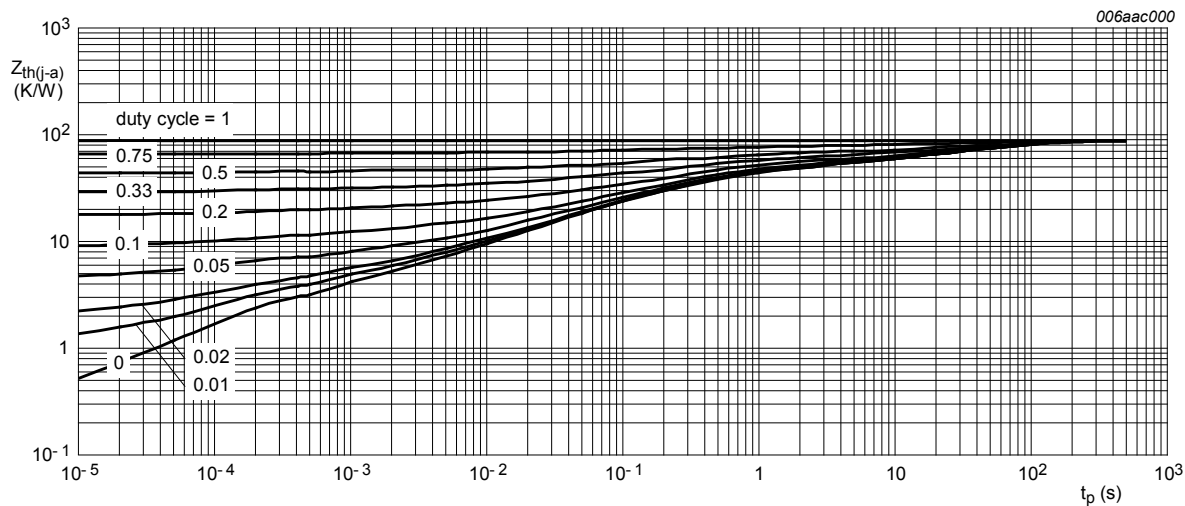


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



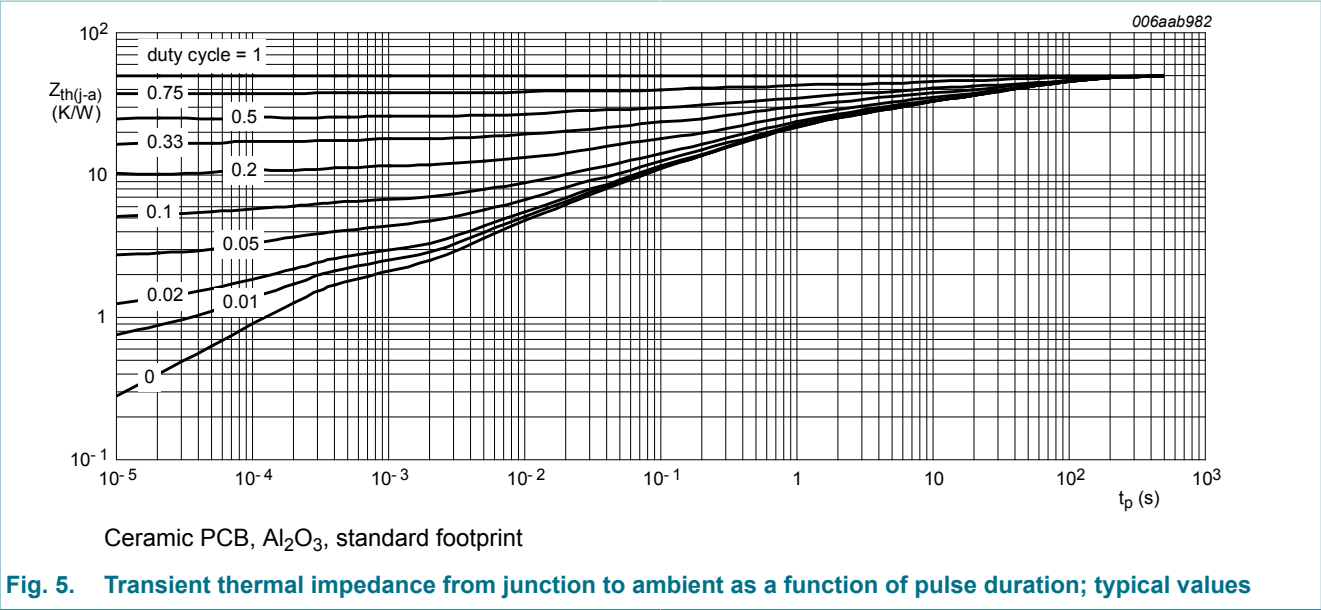
FR4 PCB, mounting pad for collector 1 cm²

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm²

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

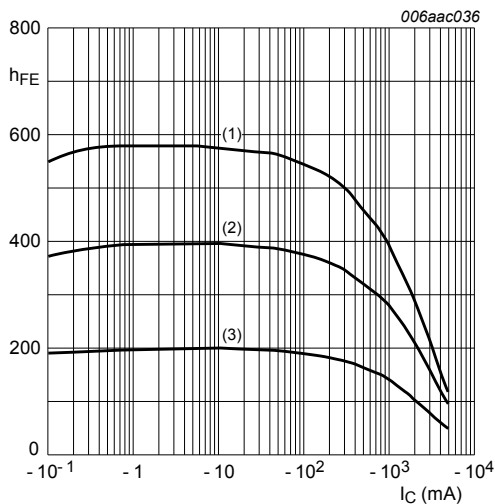


10. Characteristics

Table 7. Characteristics

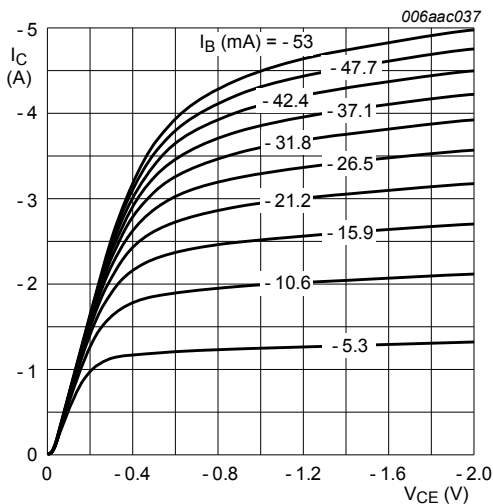
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -30\text{ V}; I_E = 0\text{ A}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-100	nA
		$V_{CB} = -30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	-50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = -24\text{ V}; V_{BE} = 0\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	-100	nA
h_{FE}	DC current gain	$V_{CE} = -2\text{ V}; I_C = -0.5\text{ A}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	200	320	-	
		$V_{CE} = -2\text{ V}; I_C = -1\text{ A}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	175	280	450	
		$V_{CE} = -2\text{ V}; I_C = -2\text{ A}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	140	210	-	
		$V_{CE} = -2\text{ V}; I_C = -3\text{ A}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	100	160	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -0.5\text{ A}; I_B = -50\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-45	-70	mV
		$I_C = -1\text{ A}; I_B = -50\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-90	-130	mV
		$I_C = -2\text{ A}; I_B = -100\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-170	-240	mV
		$I_C = -3\text{ A}; I_B = -300\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-230	-320	mV
R_{CEsat}	collector-emitter saturation resistance	$t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	75	107	m Ω
V_{BEsat}	base-emitter saturation voltage	$I_C = -2\text{ A}; I_B = -100\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-0.89	-1.1	V
		$I_C = -3\text{ A}; I_B = -300\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-0.97	-1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -1\text{ A}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-0.75	-1	V
t_d	delay time	$V_{CC} = -9\text{ V}; I_C = -2\text{ A}; I_{Bon} = -0.1\text{ A}; I_{Boff} = 0.1\text{ A}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	11	-	ns
t_r	rise time		-	59	-	ns
t_{on}	turn-on time		-	70	-	ns
t_s	storage time		-	165	-	ns
t_f	fall time		-	35	-	ns
t_{off}	turn-off time		-	200	-	ns

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_T	transition frequency	$V_{CE} = -5\text{ V}$; $I_C = -100\text{ mA}$; $f = 100\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	100	165	-	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}$; $I_E = 0\text{ A}$; $i_e = 0\text{ A}$; $f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	38	45	pF



$V_{CE} = -2\text{ V}$
(1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig. 6. DC current gain as a function of collector current; typical values



$T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig. 7. Collector current as a function of collector-emitter voltage; typical values

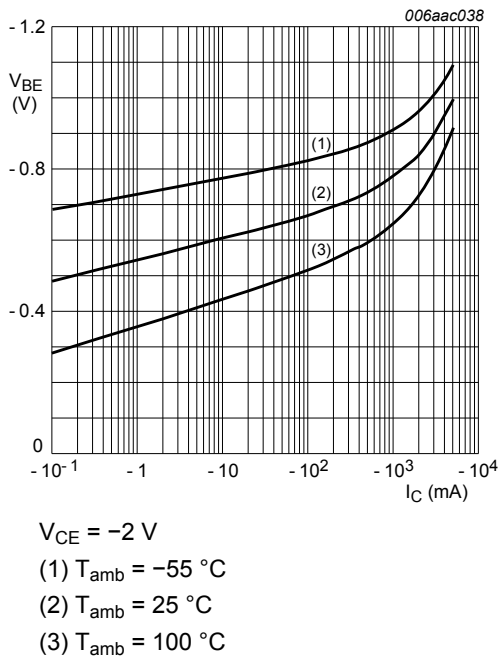


Fig. 8. Base-emitter voltage as a function of collector current; typical values

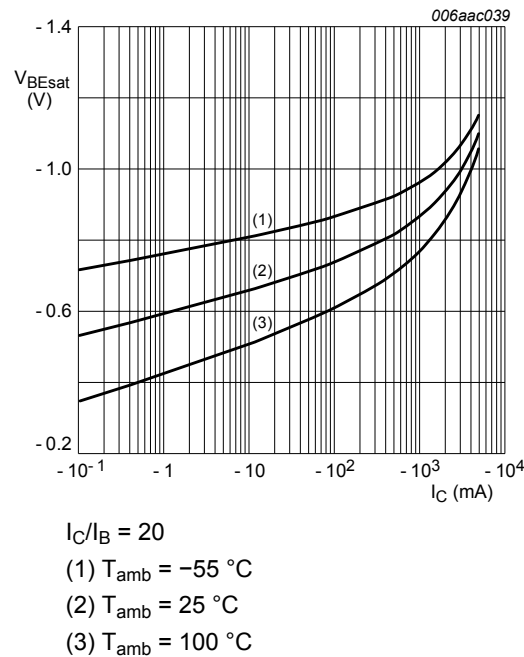


Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values

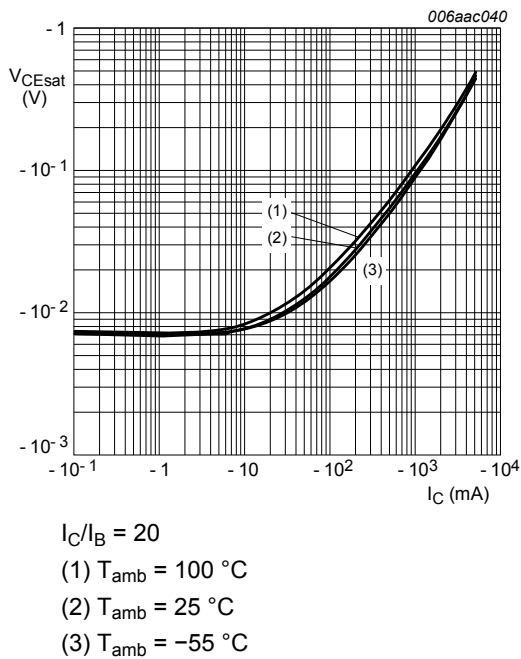


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

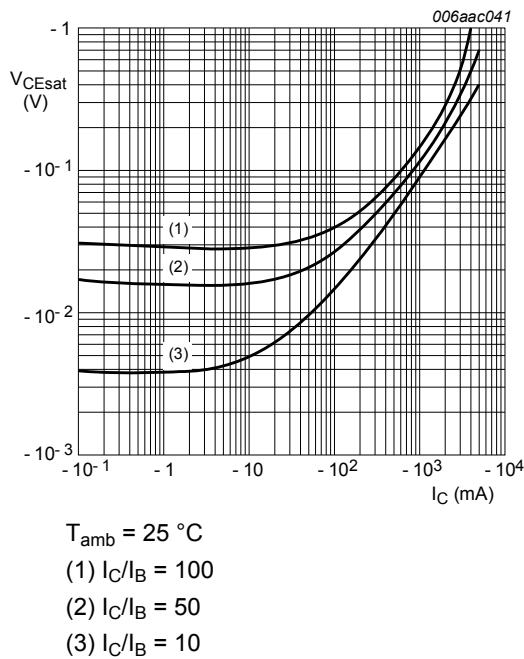


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

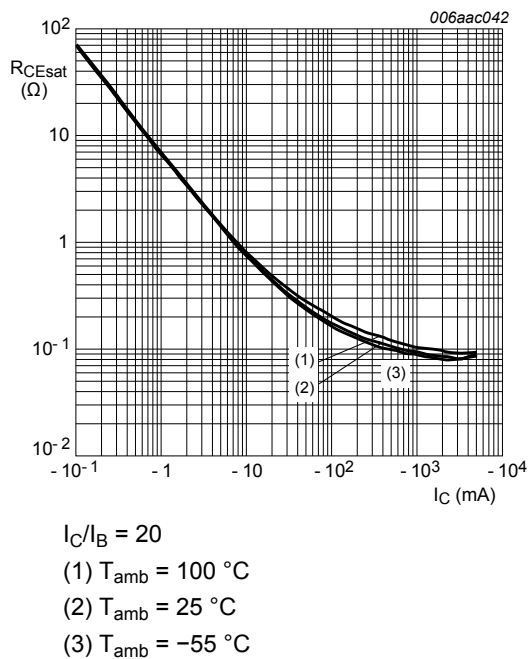


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

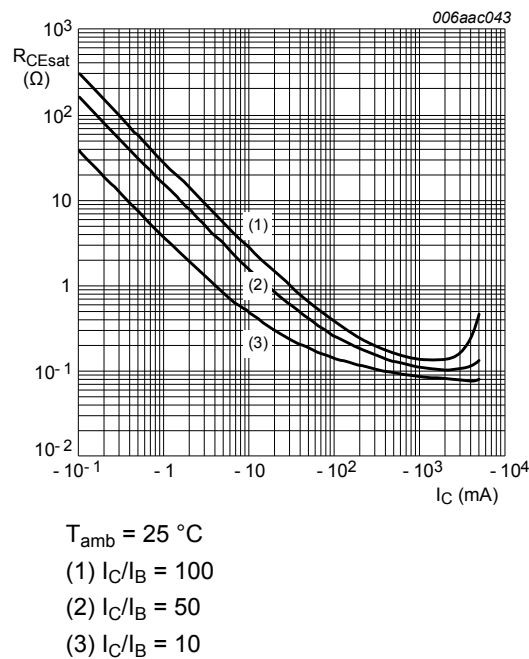


Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

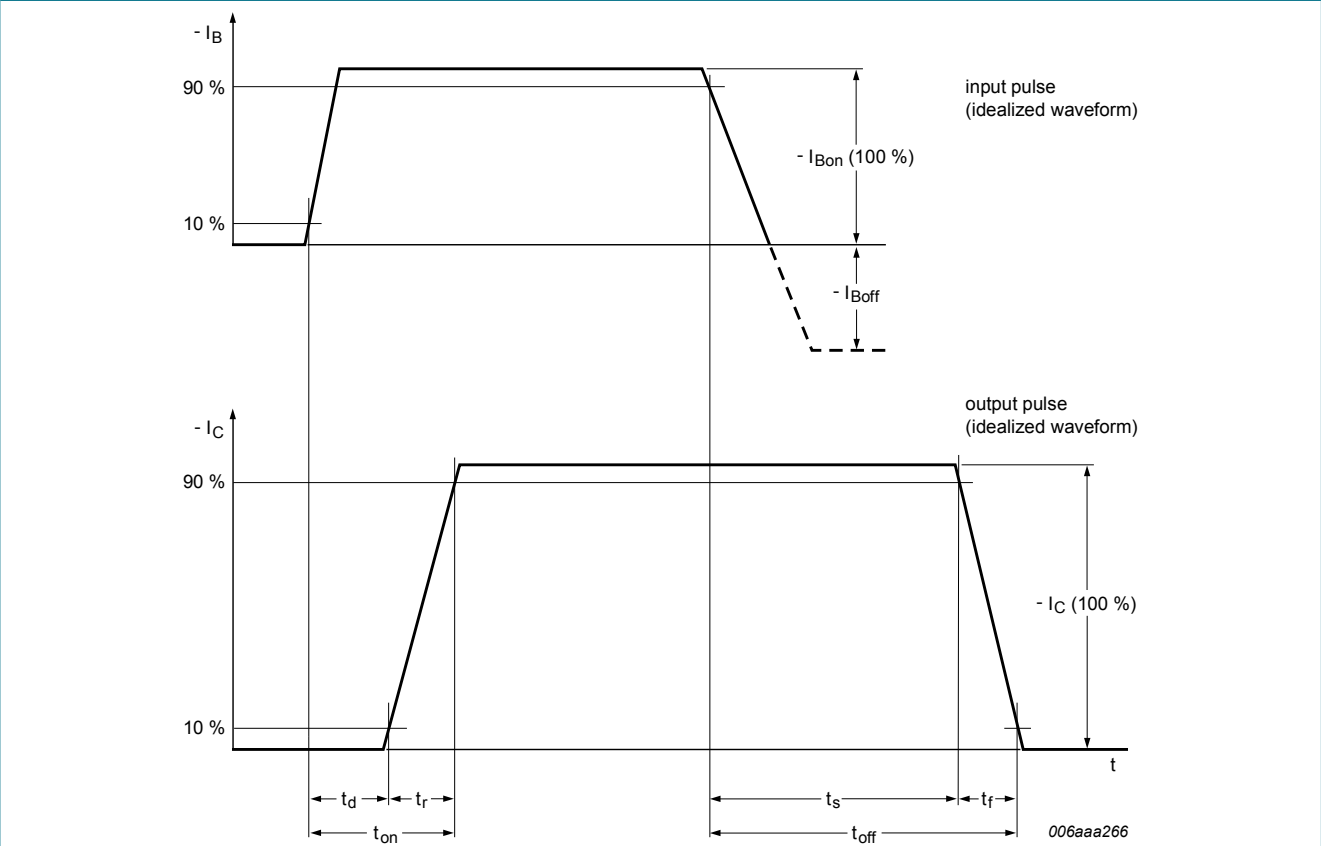


Fig. 14. BISS transistor switching time definition

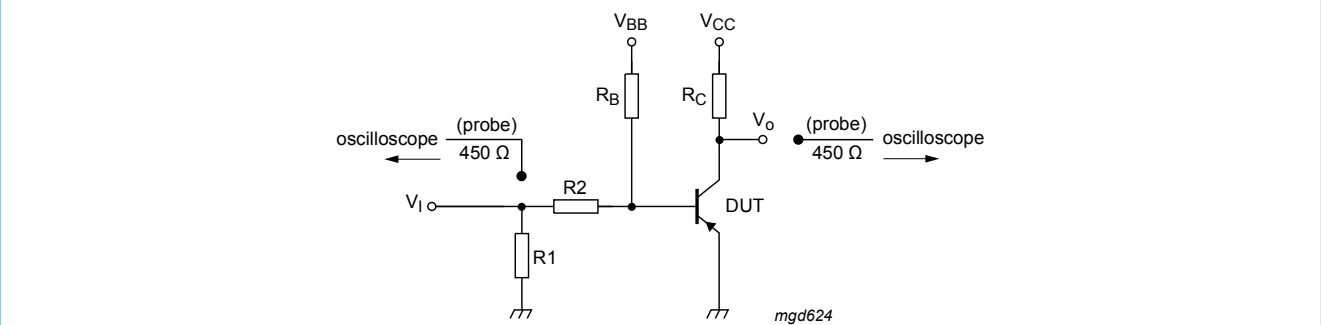


Fig. 15. Test circuit for switching times

12. Package outline

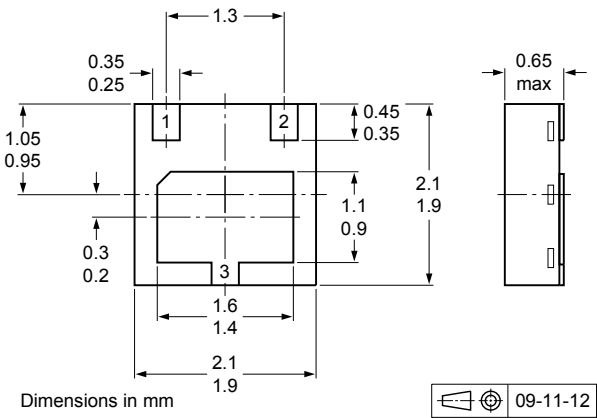


Fig. 16. Package outline DFN2020-3 (SOT1061)

13. Soldering

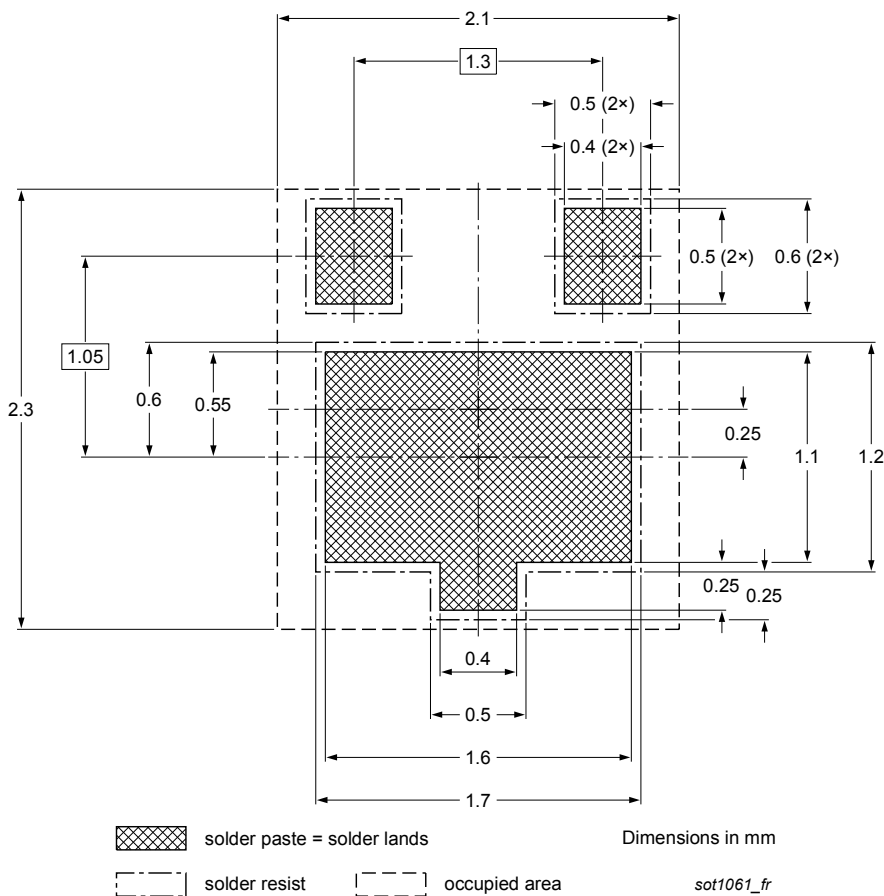


Fig. 17. Reflow soldering footprint for DFN2020-3 (SOT1061)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5330PA v.2	20150407	Product data sheet	-	PBSS5330PA v.1
Modifications:	<ul style="list-style-type: none">Condition V_{CE} changed for parameter I_{CES} in Table 7, Characteristics			
PBSS5330PA v.1	20100419	Product data sheet	-	-

15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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